BUV26

Switch-mode Series NPN Silicon Power Transistor

Designed for high-speed applications.

Features

- Switch-mode Power Supplies
- High Frequency Converters
- Relay Drivers
- Driver
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS ($T_J = 25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO(sus)}	90	Vdc
Collector-Base Voltage	V _{CBO}	180	Vdc
Emitter-Base Voltage	V _{EBO}	7.0	Vdc
Collector Current – Continuous	I _C	20	Adc
Collector Current – Peak (pw 10 ms)	I _{CM}	30	Adc
Base Current – Continuous	Ι _Β	4.0	Adc
Base Current – Peak	I _{BM}	6.0	Adc
Total Power Dissipation @ $T_C = 25^{\circ}C$ Total Power Dissipation @ $T_C = 60^{\circ}C$	P _D P _D	85 65	W W
Operating and Storage Junction Temperature Range	T _J , T _{stg}	- 65 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.76	°C/W

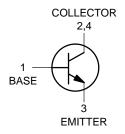


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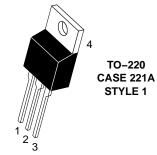
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12 AMPERES NPN SILICON POWER TRANSISTORS 90 VOLTS, 85 WATTS

SCHEMATIC



MARKING DIAGRAM





BUV26 = Device Code A = Assembly Location

ORDERING INFORMATION

Device	Package	Shipping
BUV26G	TO-220 (Pb-Free)	50 Units / Rail

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS		•	•	•	
Collector–Emitter Sustaining (I _C = 200 mA, I _B = 0, L = 29	V _{CEO(sus)}	90	_	Vdc	
Collector Cutoff Current at Re (V _{CE} = 180 V, V _{BE} = -1.5 \	I _{CEX}	-	1.0	mAdc	
Emitter Base Reverse Voltag (I _E = 50 mA)	е	V _{EBO}	7.0	30	V
Emitter Cutoff Current (V _{EB} = 5.0 V)	I _{EBO}	_	1.0	mAdc	
Collector Cutoff Current ($V_{CE} = 180 \text{ V}, R_{BE} = 50 \Omega,$	ICER	I _{CER} -		mAdc	
ON CHARACTERISTICS					
	V _{CE(sat)}	- -	0.6 1.5	Vdc	
Base–Emitter Saturation Volt (I _C = 12 A, I _B = 1.2 A)	V _{BE(sat)}	-	2.0	Vdc	
SWITCHING CHARACTERIST	TCS (Resistive Load)				
Turn On Time	$I_C = 12 \text{ A}, I_B = 1.2 \text{ A}$	t _{on}	-	0.6	μS
Storage Time	$V_{CC} = 50 \text{ V}, V_{BE} = 6.0 \text{ V}$	t _s	-	1.0	1
Fall Time	$RB2 = 2.5~\Omega$	t _f	-	0.15	
SWITCHING CHARACTERIST	TCS (Inductive Load)	<u>.</u>			-
Storage Time	$V_{CC} = 50 \text{ V, } I_{C} = 12 \text{ A}$	T _s	-	2.0	μS
Fall Time	$I_{B(end)} = 1.2 \text{ A}, V_{B} = 5.0 \text{ V}$ $L_{B} = 0.5 \text{ pH}, T_{J} = 125^{\circ}\text{C}$	T _f	-	.15	1

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse width $\leq 300~\mu s$; Duty cycle $\leq 2\%$.

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TYPICAL CHARACTERISTICS

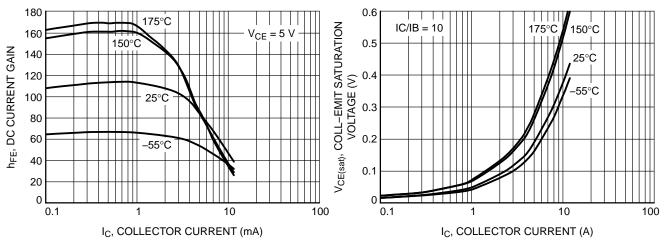


Figure 1. DC Current Gain

Figure 2. Collector-Emitter Saturation Voltage

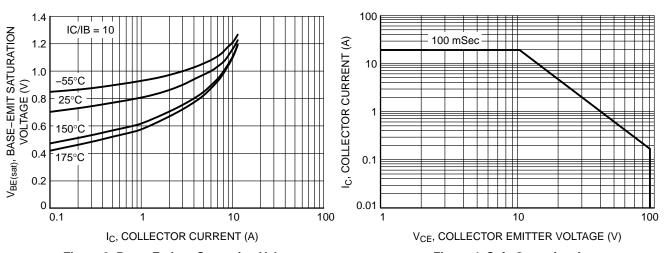
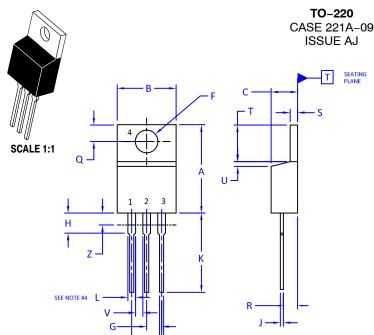


Figure 3. Base-Emitter Saturation Voltage

Figure 4. Safe Operating Area

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS





DATE 05 NOV 2019

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES

NOTES:

3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMETERS	
DIM	MIN.	MAX.	MIN.	MAX.
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
К	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:	
PIN 1.	BASE	PIN 1.	BASE	PIN 1.	CATHODE	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	EMITTER	2.	ANODE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	COLLECTOR	3.	GATE	3.	GATE
4.	COLLECTOR	4.	EMITTER	4.	ANODE	4.	MAIN TERMINAL 2
STYLE 5:		STYLE 6:		STYLE 7:		STYLE 8:	
PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	CATHODE	PIN 1.	CATHODE
2.	DRAIN	2.	CATHODE	2.	ANODE	2.	ANODE
3.	SOURCE	3.	ANODE	3.	CATHODE	3.	EXTERNAL TRIP/DELA
4.	DRAIN	4.	CATHODE	4.	ANODE	4.	ANODE
STYLE 9:		STYLE 10:		STYLE 11:		STYLE 12	:
PIN 1.	GATE	PIN 1.	GATE	PIN 1.	DRAIN	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	SOURCE	2.	SOURCE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	DRAIN	3.	GATE	3.	GATE
4.	COLLECTOR	4.	SOURCE	4.	SOURCE	4.	NOT CONNECTED

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